



N 沟道增强型场效应晶体管

N-CHANNEL MOSFET

FHP250N6F2A

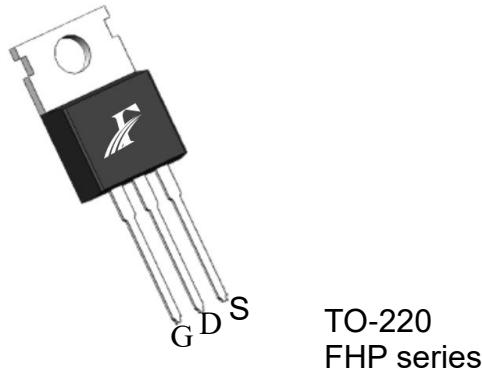
主要参数 MAIN CHARACTERISTICS

ID (Silicon limit)	247 A
VDSS	60 V
Rdson-typ (@Vgs=10V)	1.88 mΩ
Qg-typ	77 nC

用途 APPLICATIONS

UPS不间断电源	Uninterruptible Power Supplies
直流转换器	DC-DC Converter
逆变电源	Power management for inverter systems

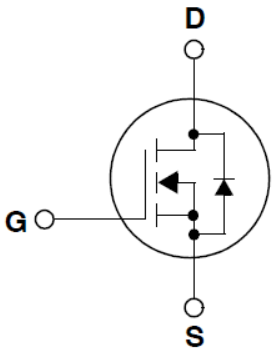
封装形式 Package



产品特性 FEATURES

低栅极电荷	Low gate charge
低 Crss (典型值 115 pF)	Low Crss (typical 115 pF)
开关速度快	Fast switching
100%经过 Rg 测试	100% Rg tested
100%经过雪崩测试	100% avalanche tested
100%经过热阻测试	100% DVDS tested
SGT 工艺	SGT process
符合 RoHS 标准	ROHS compliant

等效电路 Equivalent Circuit



绝对最大额定值 ABSOLUTE RATINGS (Tc=25℃)

项目 Parameter	符号 Symbol	数值 Value	单位 Unit
		FHP250N6F2A	
最高漏极—源极直流电压 Drain-Source Voltage	VDS	60	V
连续漏极电流* Drain Current -continuous *	ID(TC=25℃) (Silicon limit)	247	A
	ID(TC=25℃) (Package limit)	120	
	ID(TC=100℃) (Silicon limit)	157	
最大脉冲漏极电流 (注 1) Drain Current – pulse (note 1)	IDM	480	A
最高栅源电压 Gate-Source Voltage	VGS	±20	V
单脉冲雪崩能量 (注 2) Single Pulsed Avalanche Energy (note 2)	EAS	450	mJ
雪崩电流 (注 1) Avalanche Current (note 1)	IAR	30	A
二极管反向恢复最大电压变化速率 (注 3) Peak Diode Recovery dv/dt (note 3)	dv/dt	5.0	V/ns
耗散功率 Power Dissipation	Pd (TC=25℃)	249	W
	-Derate above 25℃	2.0	W/℃
最高结温及存储温度 Operating and Storage Temperature Range	TJ, TSTG	150, -55~+150	℃
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	TL	260	℃

*漏极电流由最高结温限制

*Drain current limited by maximum junction temperature

电特性 ELECTRICAL CHARACTERISTICS

项目 Parameter	符号 Symbol	测试条件 Tests conditions	最小 Min	典型 Typ	最大 Max	单位 Units
关态特性 Off –Characteristics						
漏－源击穿电压 Drain-Source Voltage	BV _{DSS}	I _D =250μA, V _{GS} =0V	60	-	-	V
击穿电压温度特性 Breakdown Voltage Temperature Coefficient	ΔBV _{DSS} /Δ T _J	I _D =250μA, referenced to 25℃	-	0.06	-	V/℃
零栅压下漏极漏电流 Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V, T _C =25℃	-	-	1	μA
		V _{DS} =48V, T _C =125℃	-	-	100	μA
栅极体漏电流 Gate-body leakage current	I _{GSS} (F/R)	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
通态特性 On-Characteristics						
阈值电压 Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =250μA	2.0	-	4.0	V
静态导通电阻 Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =10V , I _D =50A	-	1.88	2.2	mΩ
动态特性 Dynamic Characteristics						
栅电阻 Gate Resistance	R _g	f=1.0MHz,V _{DS} OPEN	-	0.7	-	Ω
输入电容 Input capacitance	C _{iss}	V _{DS} =30V, V _{GS} =0V, f=1.0MHz	-	5072	-	pF
输出电容 Output capacitance	C _{oss}		-	1273	-	
反向传输电容 Reverse transfer capacitance	C _{rss}		-	115	-	
开关特性 Switching Characteristics						
延迟时间 Turn-On delay time	t _{d(on)}	V _{DD} =30V, I _D =50A, R _G =2.5Ω V _{GS} =10V (note 4, 5)	-	23	-	ns
上升时间 Turn-On rise time	t _r		-	21	-	ns
延迟时间 Turn-Off delay time	t _{d(off)}		-	35	-	ns
下降时间 Turn-Off Fall time	t _f		-	12	-	ns
栅极电荷总量 Total Gate Charge	Q _g	V _{DS} =30V , I _D =50A , V _{GS} =10V (note 4, 5)	-	77	-	nC
栅－源电荷 Gate-Source charge	Q _{gs}		-	27	-	nC
栅－漏电荷 Gate-Drain charge	Q _{gd}		-	10	-	nC
漏－源二极管特性及最大额定值 Drain-Source Diode Characteristics and Maximum Ratings						
正向最大连续电流 Maximum Continuous Drain -Source Diode Forward Current	I _S		-	-	120	A
正向最大脉冲电流 Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}		-	-	480	A
正向压降 Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =50A	-	-	1.2	V
反向恢复时间 Reverse recovery time	t _{rr}	V _{GS} =0V, I _S =50A ,dI _F /dt=100A/μs (note 4)	-	88	-	ns
反向恢复电荷 Reverse recovery charge	Q _{rr}		-	252	-	nC

热特性 THERMAL CHARACTERISTIC

项目 Parameter	符号 Symbol	FHP250N6F2A	单位 Unit
结到管壳的热阻 Thermal Resistance, Junction to Case	Rth(j-c)	0.5	℃/W
结到环境的热阻 Thermal Resistance, Junction to Ambient	Rth(j-A)	62.5	℃/W

注释：
1：脉冲宽度由最高结温限制
2：L=1mH, IAS=30A, VDD=50V, RG=25 Ω,起始结温 TJ=25℃
3：ISD ≤120A,di/dt ≤300A/μs,VDD≤BVDSS,起始结温 TJ=25℃
4：脉冲测试：脉冲宽度 ≤300μs,占空比≤2％
5：基本与工作温度无关

Notes:
1: Pulse width limited by maximum junction temperature
2: L=1mH, IAS=30A, VDD=50V, RG=25 Ω,Starting TJ=25℃
3: ISD ≤120A,di/dt ≤300A/μs,VDD≤BVDSS, Starting TJ=25℃
4: Pulse Test: Pulse Width ≤300μs,Duty Cycle≤2％
5: Essentially independent of operating temperature

Typical Performance Characteristics

Fig 1: Output Characteristics

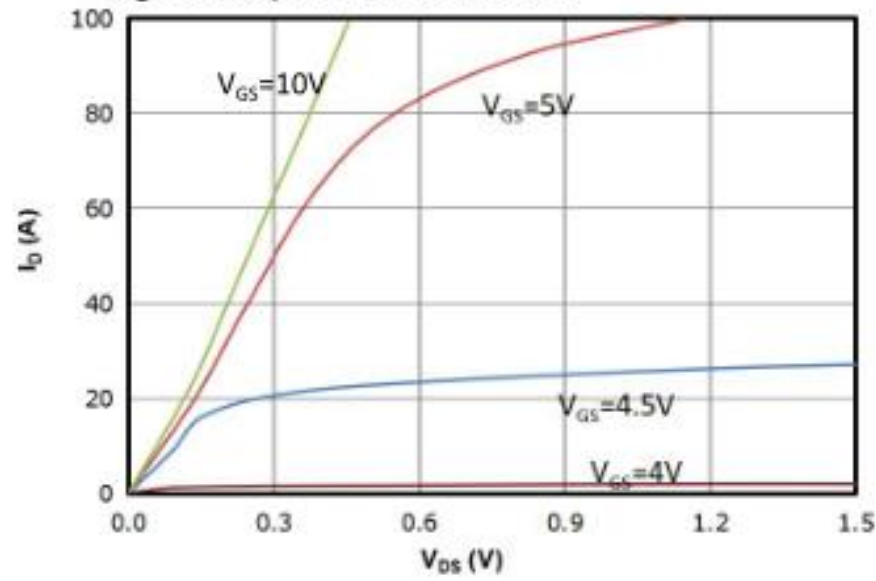


Fig 2: Transfer Characteristics

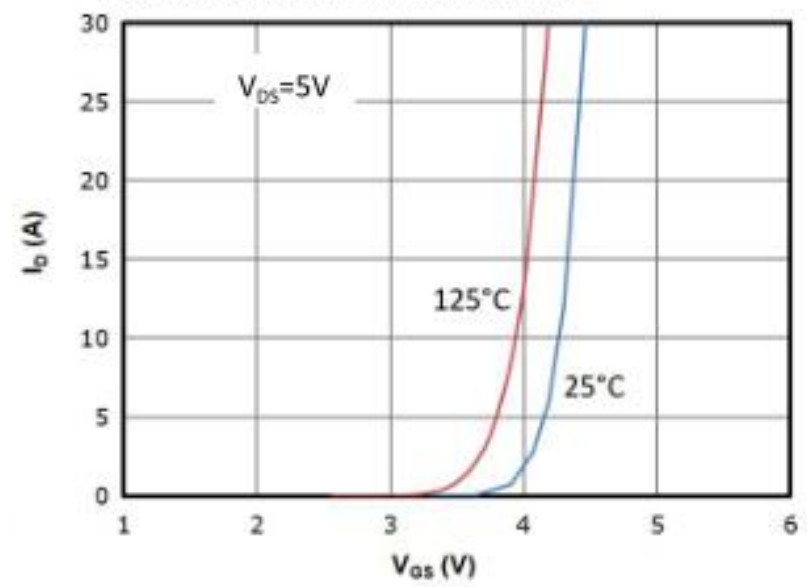


Fig 3: $R_{DS(on)}$ vs Drain Current and Gate Voltage

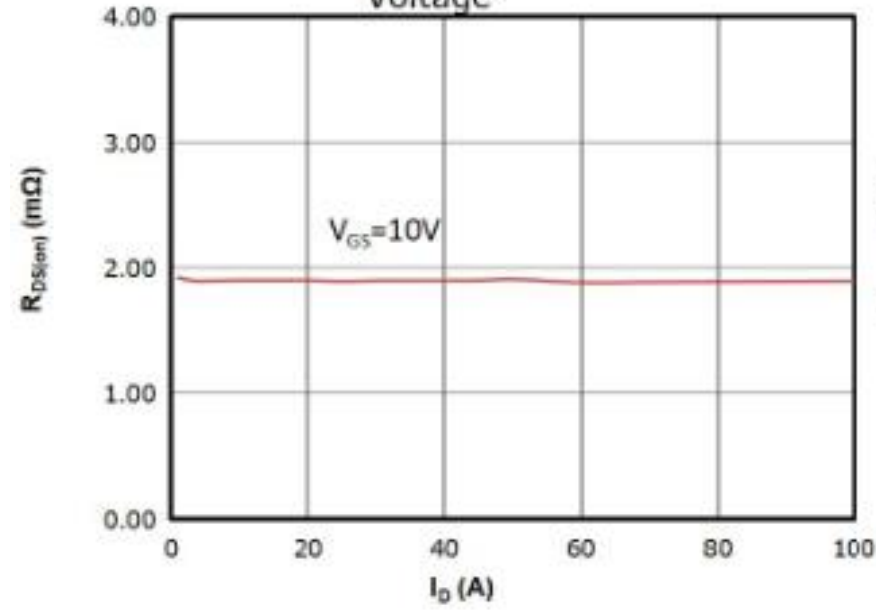


Fig 4: $R_{DS(on)}$ vs Gate Voltage

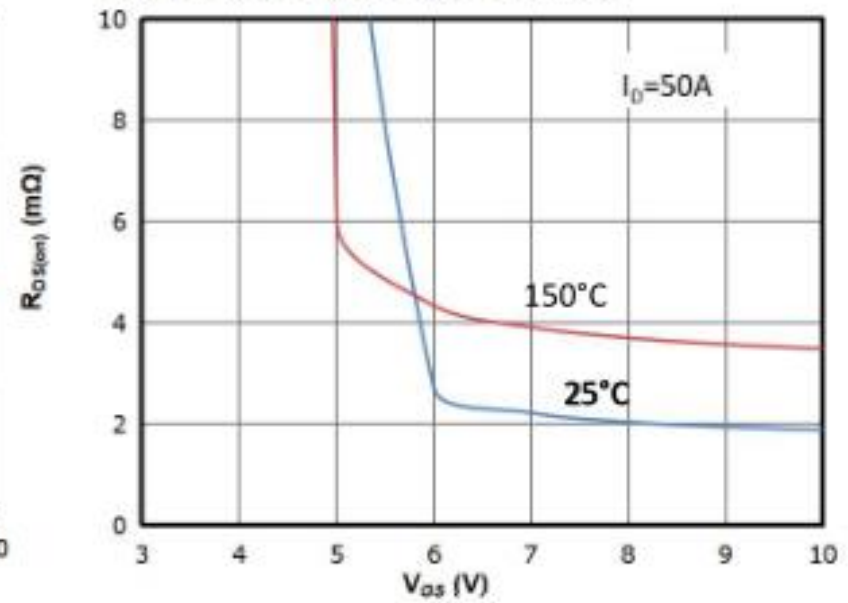


Fig 5: $R_{DS(on)}$ vs. Temperature

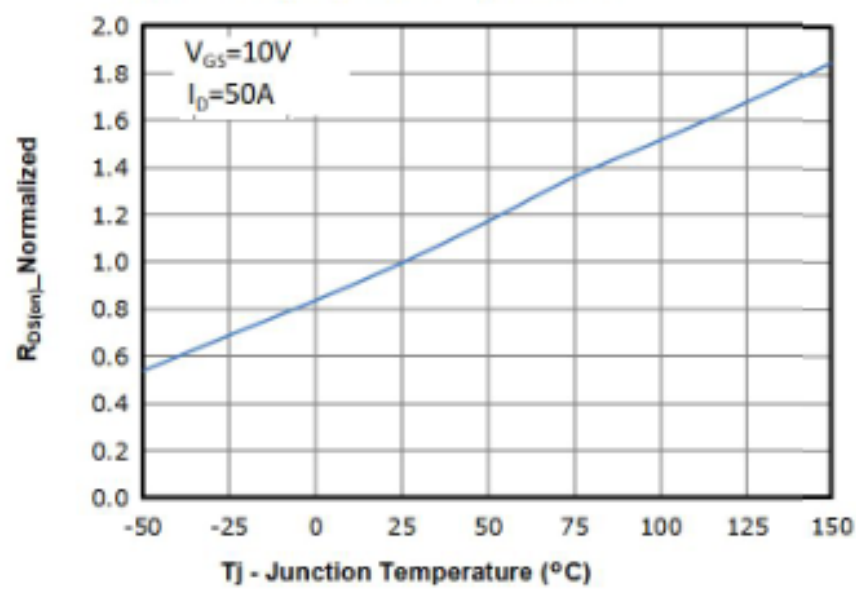
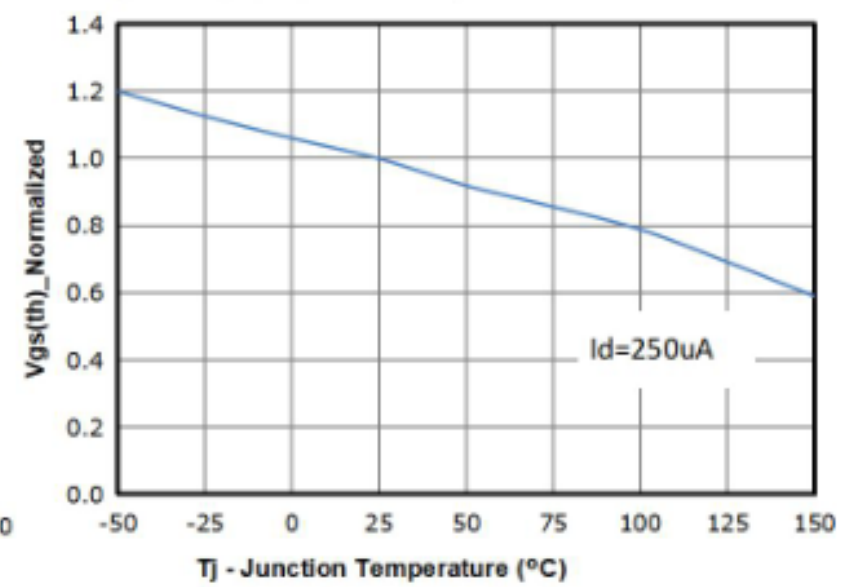
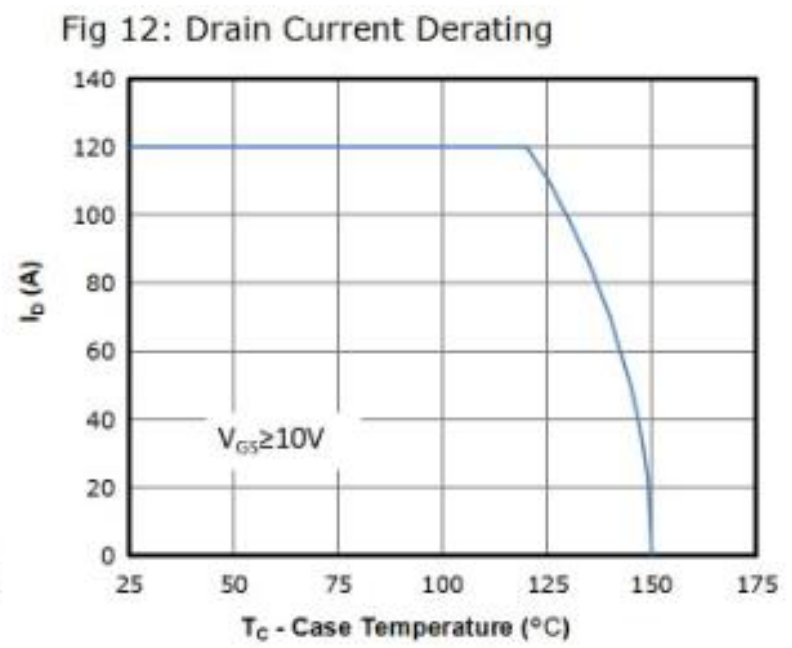
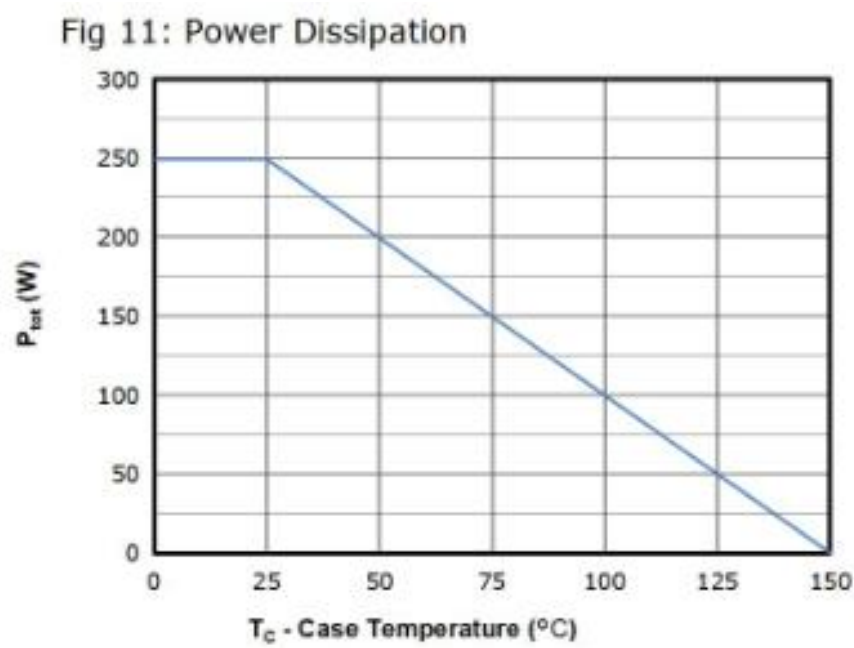
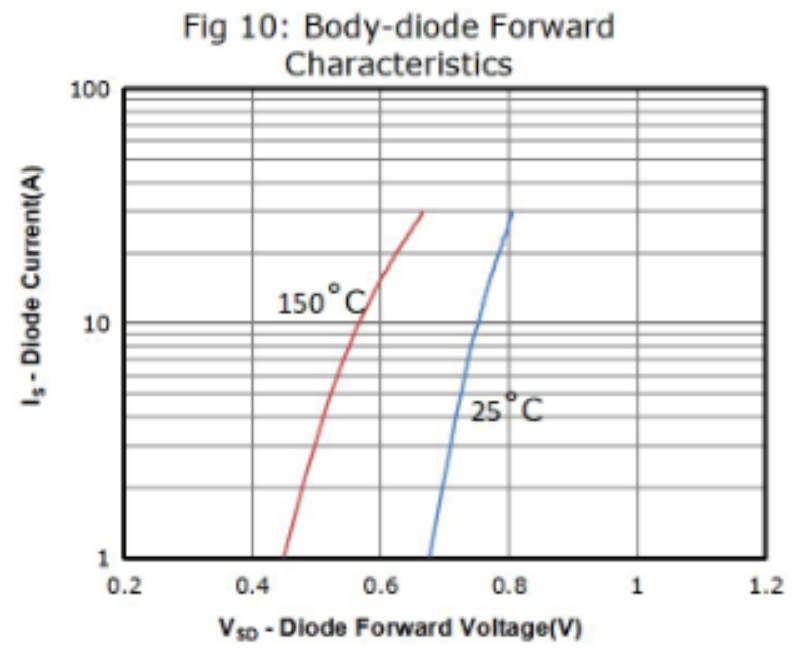
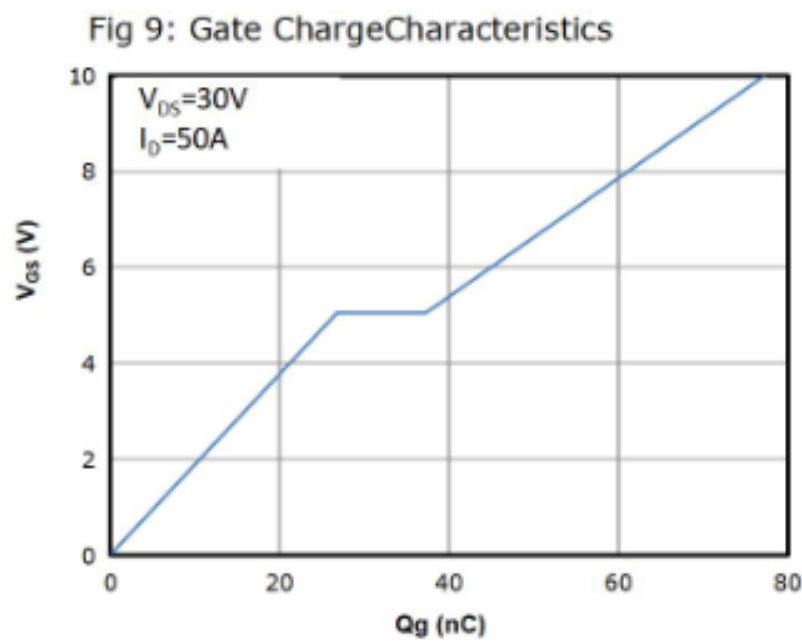
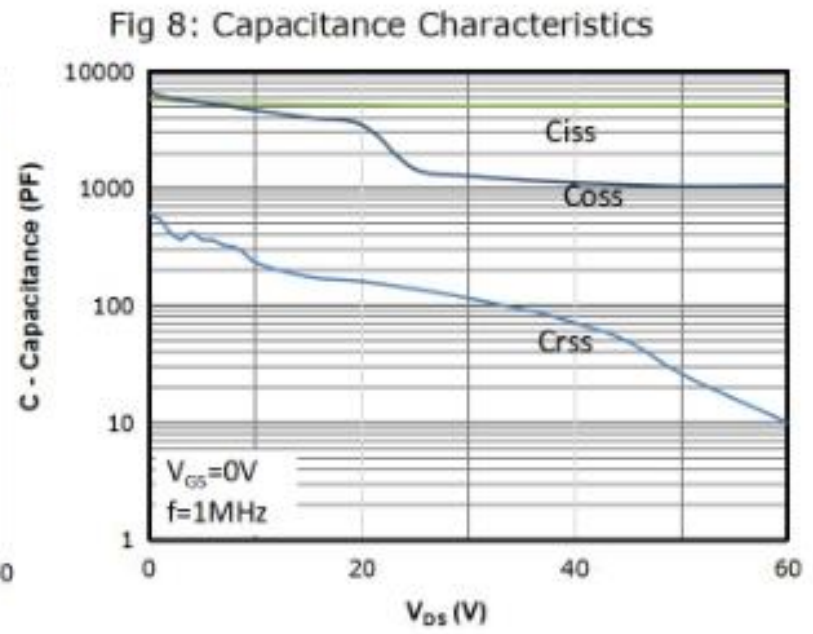
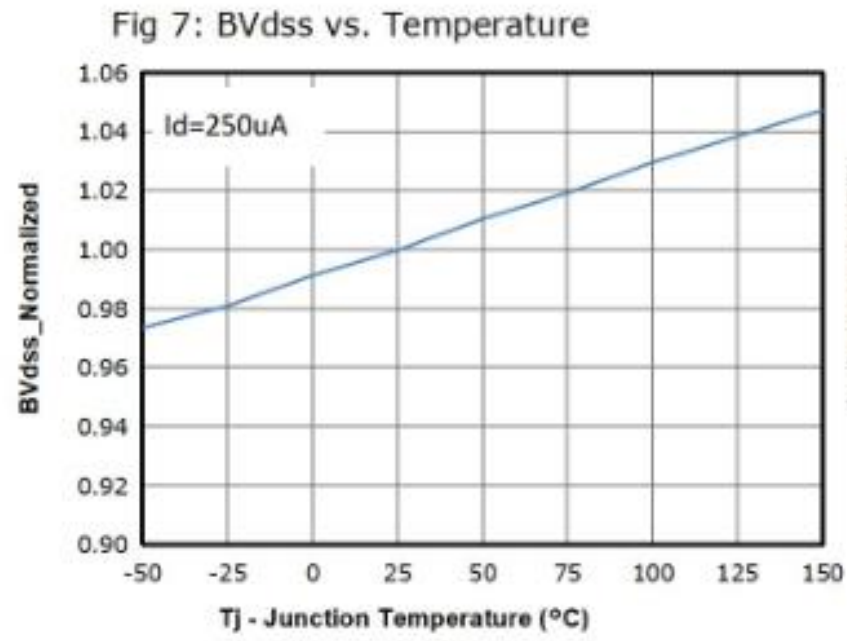
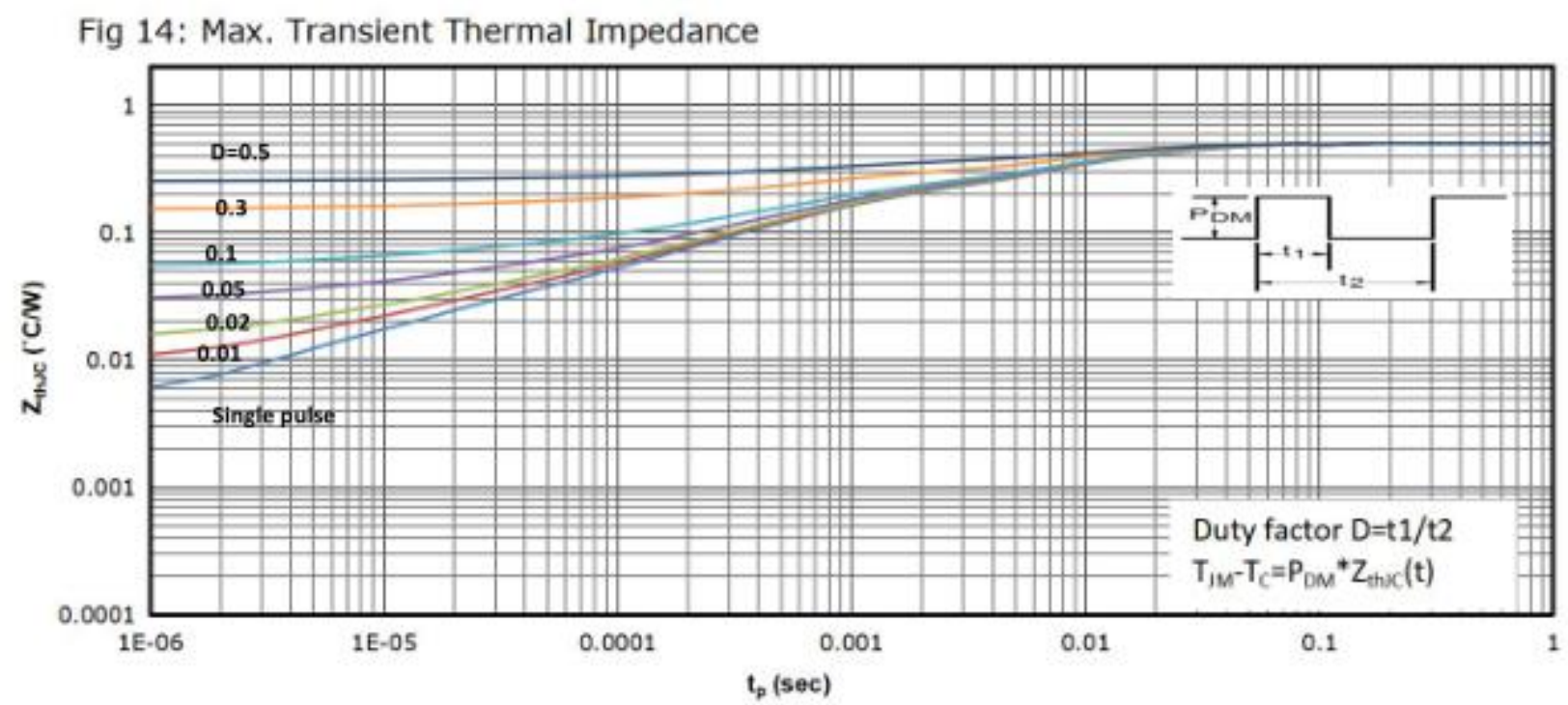
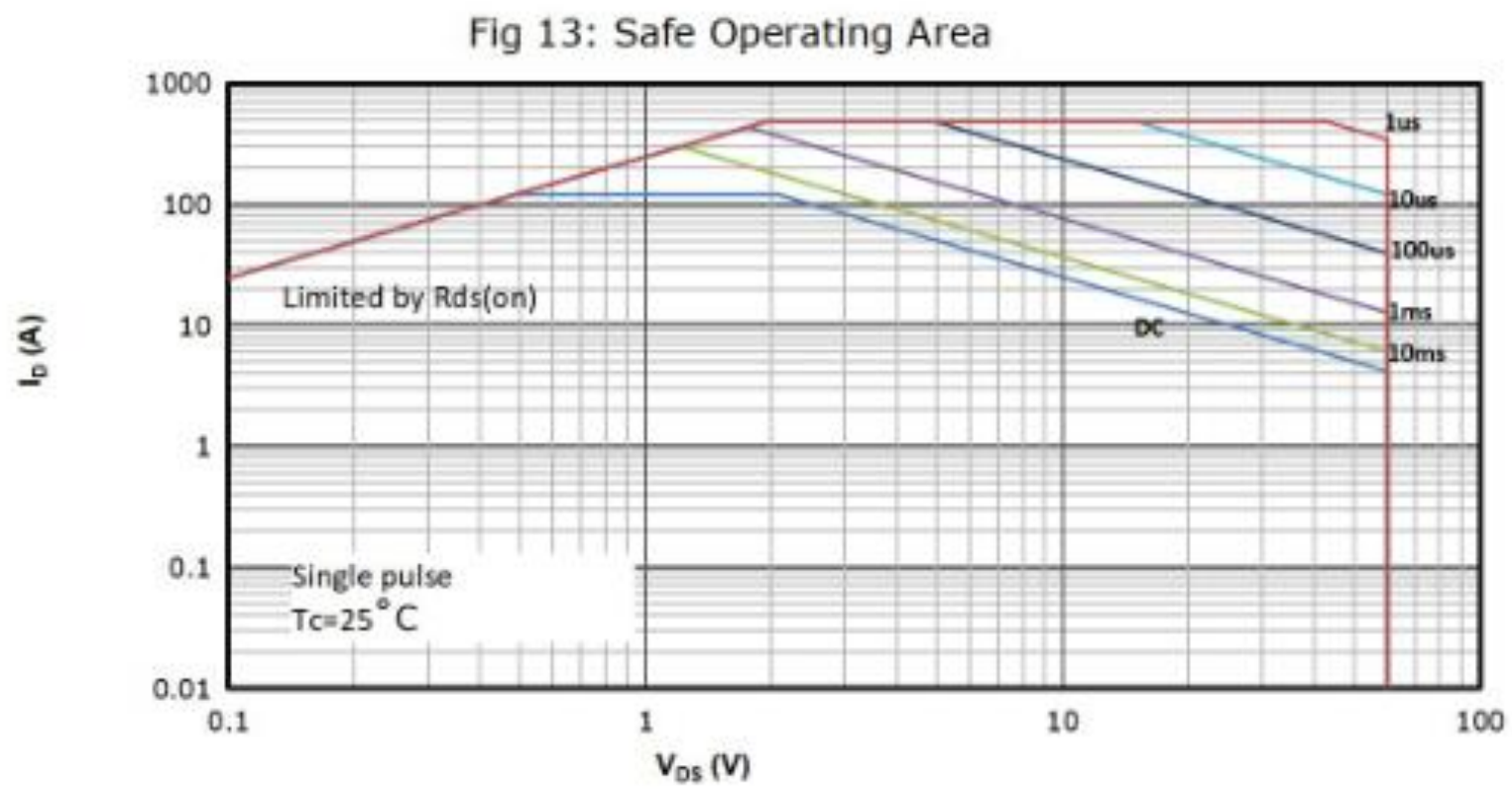


Fig 6: $V_{GS(th)}$ vs. Temperature

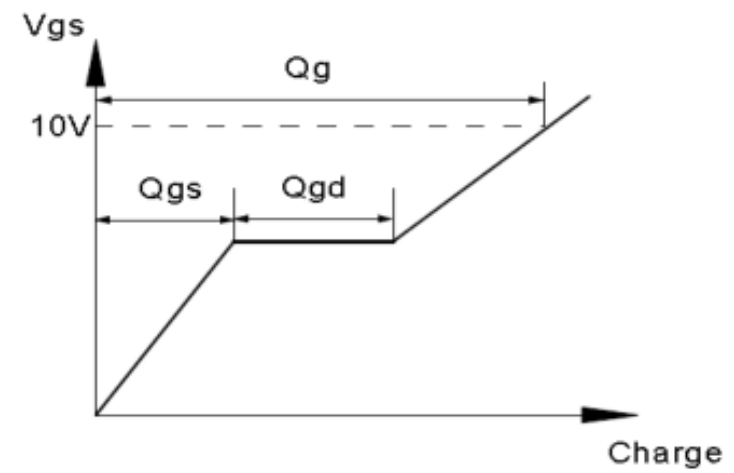
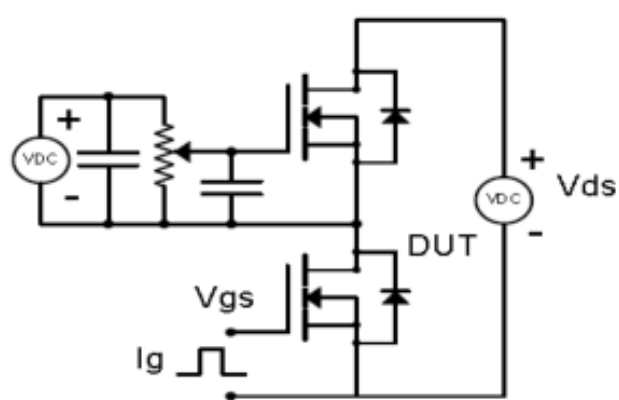




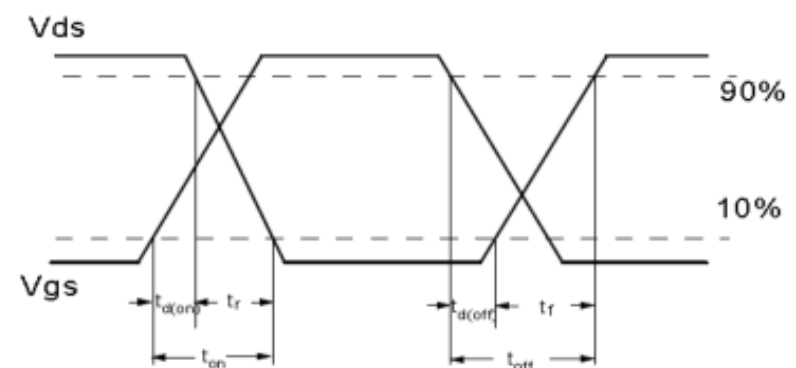
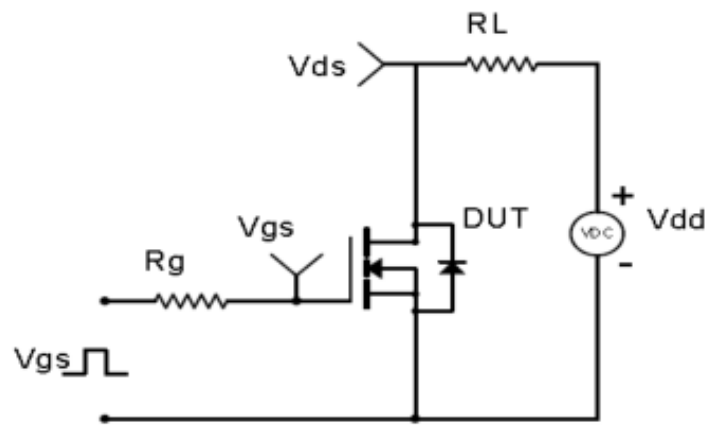


Test Circuit & Waveform

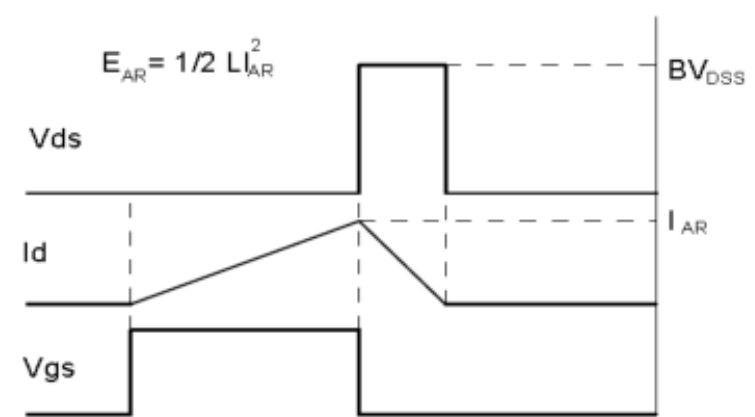
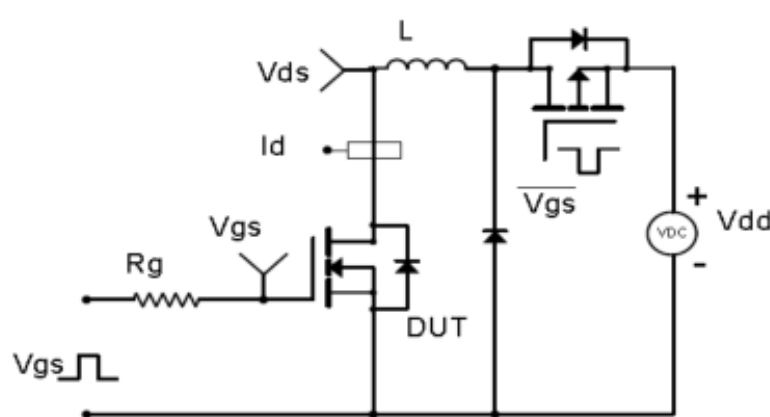
Gate Charge Test Circuit & Waveform



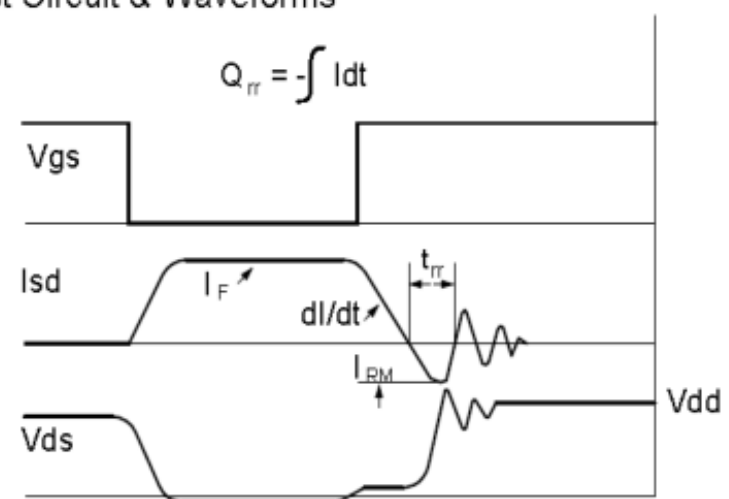
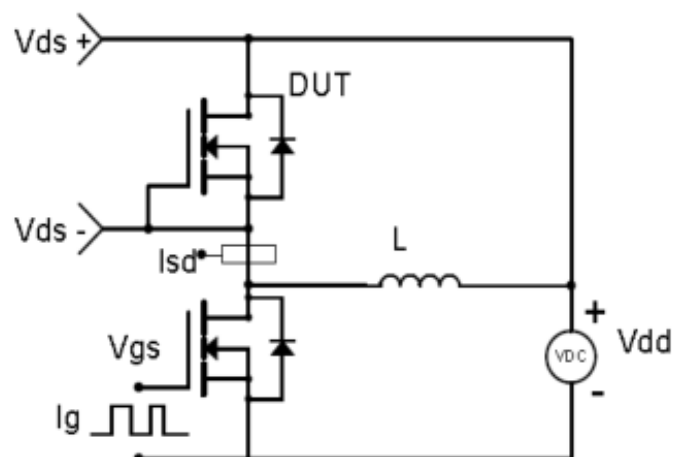
Resistive Switching Test Circuit & Waveforms



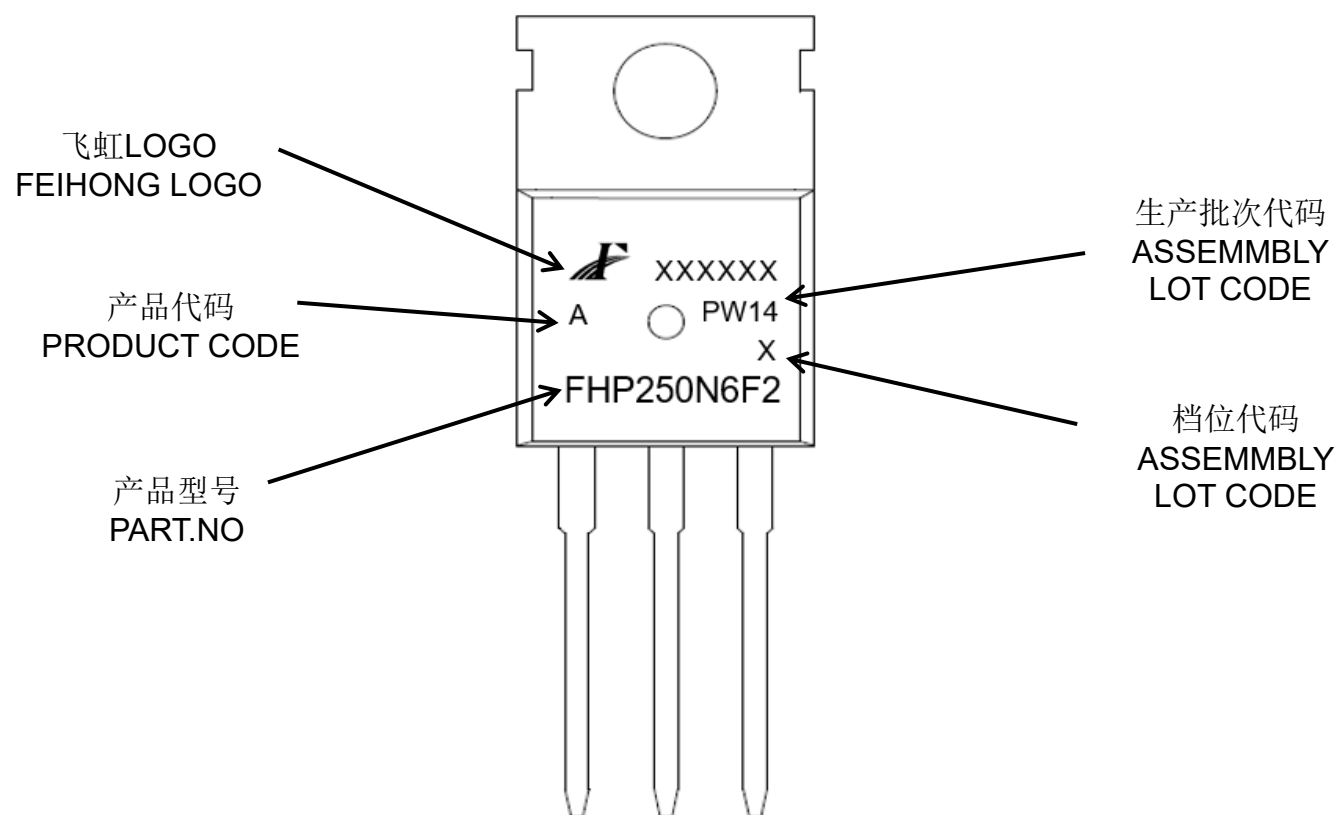
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



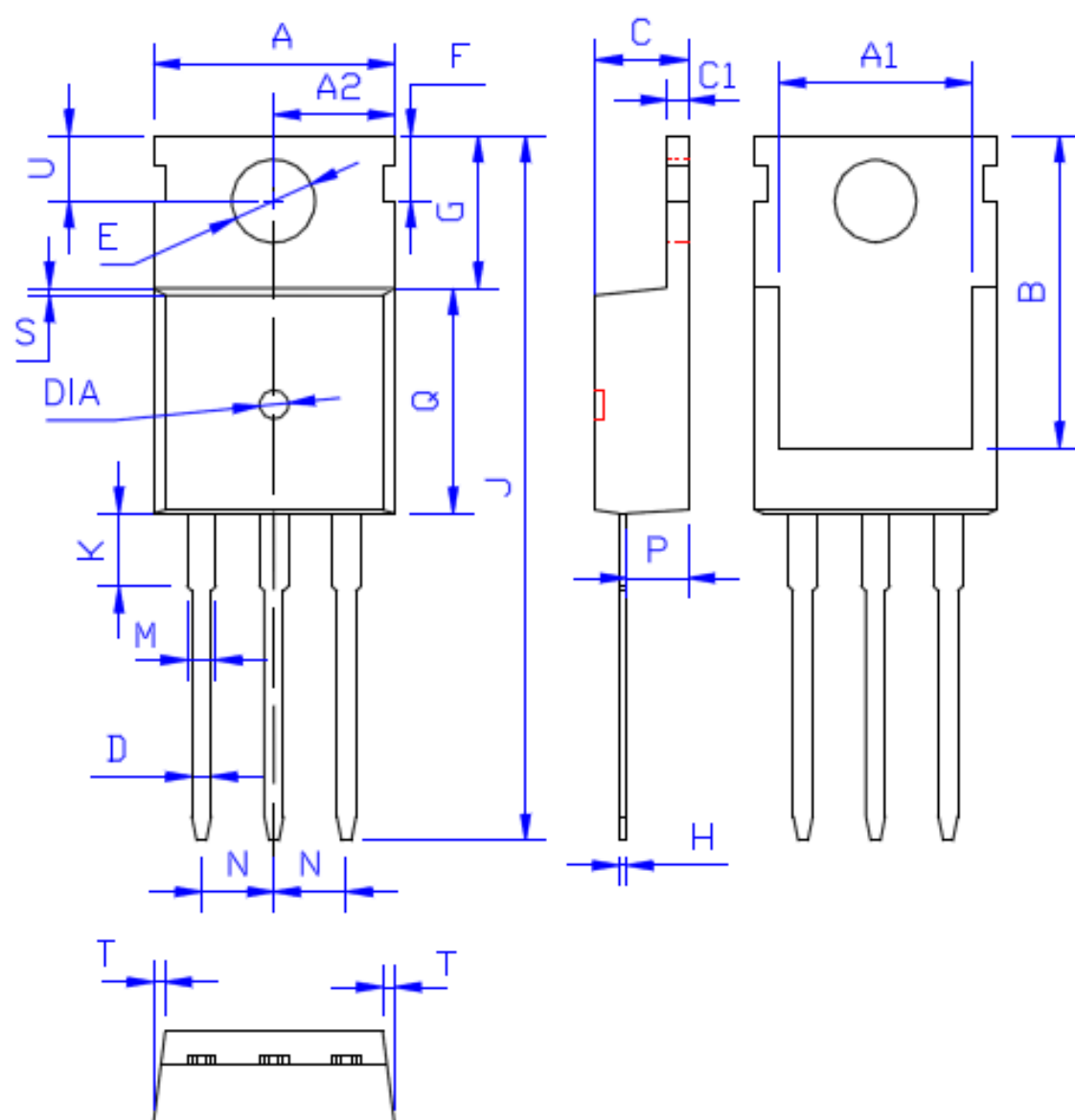
印记 Marking:



外形尺寸:

Package Dimension:

TO-220



DIM	MILLIMETERS
A	10.00±0.30
A1	8.00±0.30
A2	5.00±0.30
B	13.20±0.40
C	4.50±0.20
C1	1.30±0.20
D	0.80±0.20
E	3.60±0.20
F	3.00±0.30
G	6.60±0.40
H	0.50±0.20
J	28.88±0.50
K	3.00±0.30
M	1.30±0.30
N	Typical 2.54
P	2.40±0.40
Q	9.20±0.40
S	0.25±0.15
T	0.25±0.15
U	2.80±0.30
DIA	宽 1.50±0.10 深 0.50 MAX

(Unit: mm)